

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

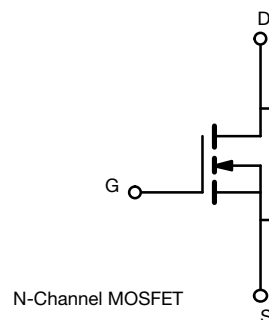
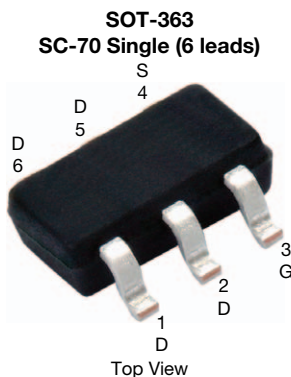
PRODUCT SUMMARY

V _{DS} (V)	60
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.120
R _{DS(on)} (Ω) at V _{GS} = 4.5 V	0.150
I _D (A)	1.7
Configuration	Single
Package	SC-70

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified ^d
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912

AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE

Marking Code: 9G

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current ^a	I _D	T _C = 25 °C	1.7
		T _C = 125 °C	1.7
Continuous Source Current (Diode Conduction) ^a	I _S	1.7	A
Pulsed Drain Current ^b	I _{DM}	6.7	
Single Pulse Avalanche Current	I _{AS}	10	
Single Pulse Avalanche Energy	E _{AS}	5	mJ
Maximum Power Dissipation ^b	P _D	T _C = 25 °C	3.3
		T _C = 125 °C	1.1
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R _{thJA}	125	°C/W
Junction-to-Foot (Drain)	R _{thJF}	45	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).
- Parametric verification ongoing.

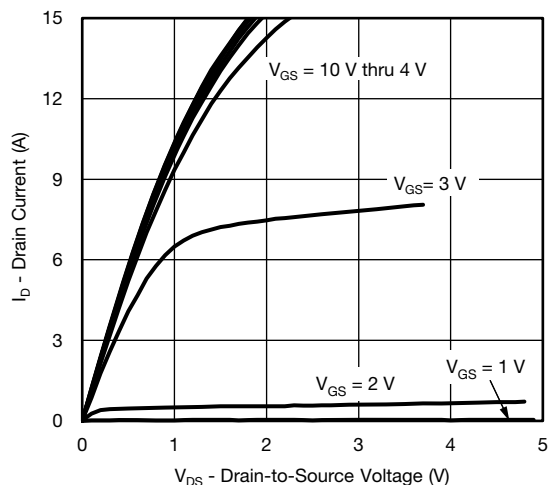
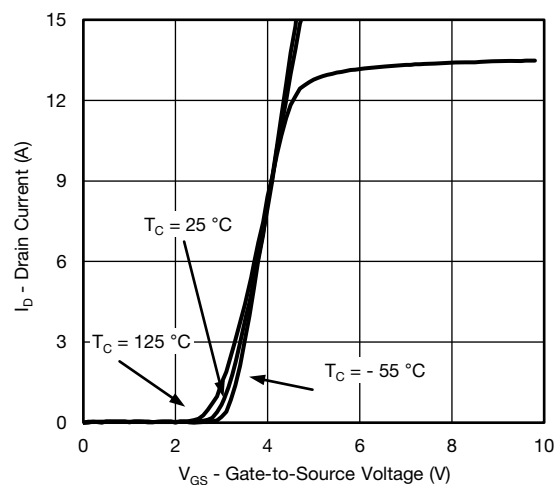
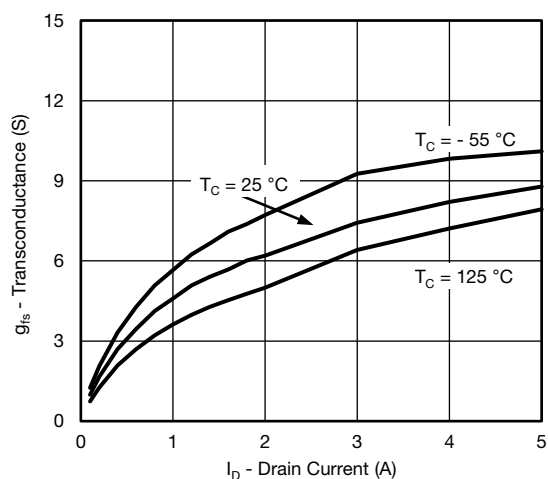
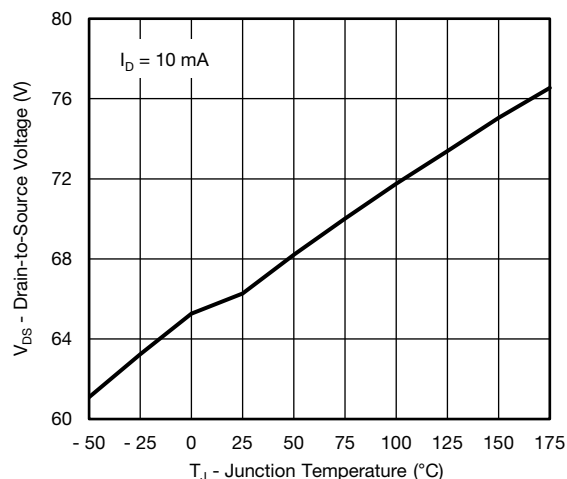
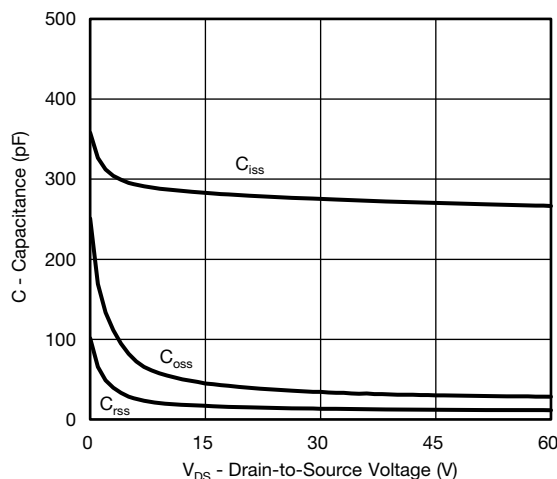
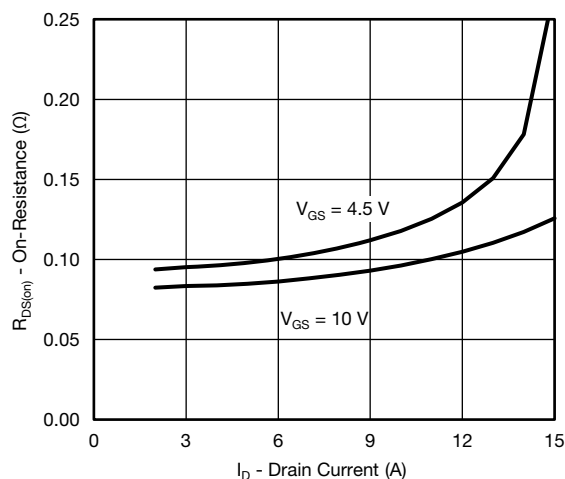


SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.5	2	2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	10	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 3.8 A	-	0.085	0.120	Ω
		V _{GS} = 10 V	I _D = 3.8 A, T _J = 125 °C	-	-	0.200	
		V _{GS} = 10 V	I _D = 3.8 A, T _J = 175 °C	-	-	0.240	
		V _{GS} = 4.5 V	I _D = 3.1 A	-	0.095	0.150	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 1.8 A		-	6	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 15 V, f = 1 MHz	-	275	344	pF
Output Capacitance	C _{oss}			-	34	42	
Reverse Transfer Capacitance	C _{rss}			-	13	17	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 30 V, I _D = 3.8 A	-	4.4	5.5	nC
Gate-Source Charge	Q _{gs}			-	0.7	-	
Gate-Drain Charge ^c	Q _{gd}			-	1.3	-	
Gate Resistance	R _g	f = 1 MHz		2.1	4.1	6.2	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 3.9 Ω I _D ≅ 3.8 A, V _{GEN} = 10 V, R _g = 1 Ω		-	5.8	7.3	ns
Rise Time ^c	t _r			-	23	29	
Turn-Off Delay Time ^c	t _{d(off)}			-	10	13	
Fall Time ^c	t _f			-	30	39	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	11	A
Forward Voltage	V _{SD}	I _F = 1.8 A, V _{GS} = 0 V		-	0.8	1.2	V

Notes

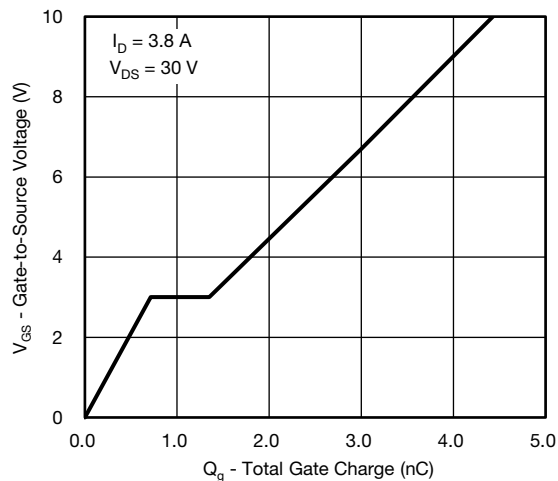
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

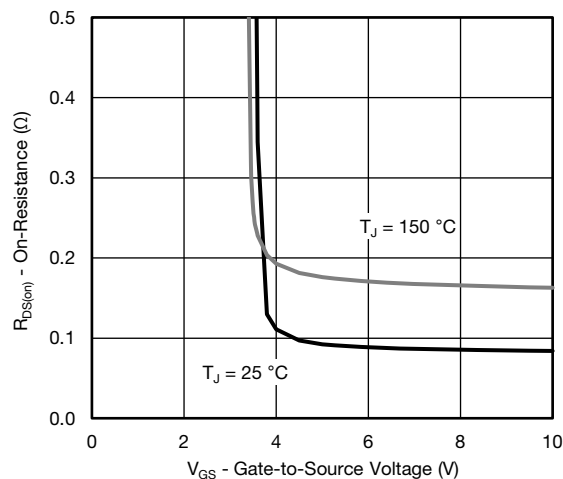
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

Drain Source Breakdown vs. Junction Temperature

Capacitance

On-Resistance vs. Drain Current



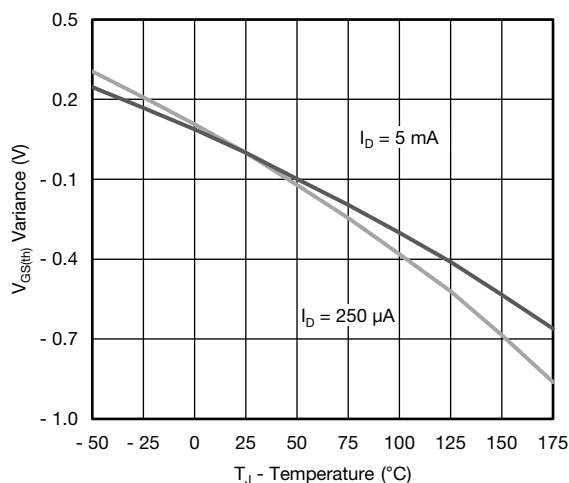
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



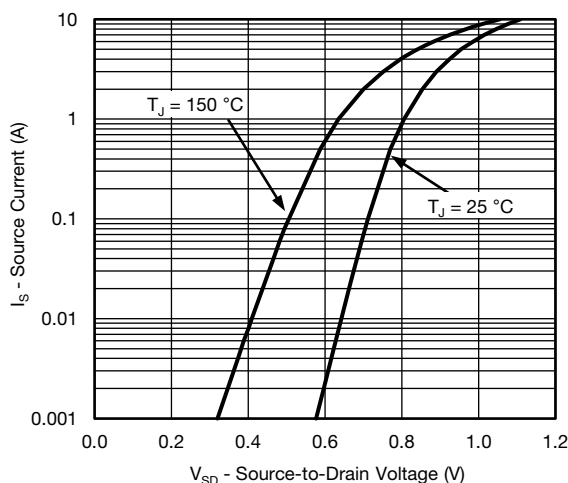
Gate Charge



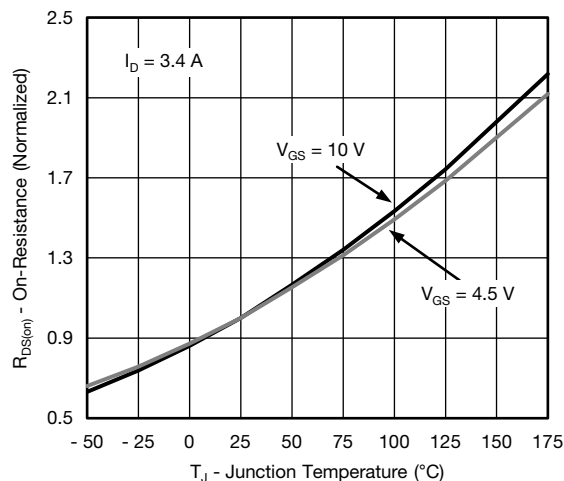
On-Resistance vs. Gate-to-Source Voltage



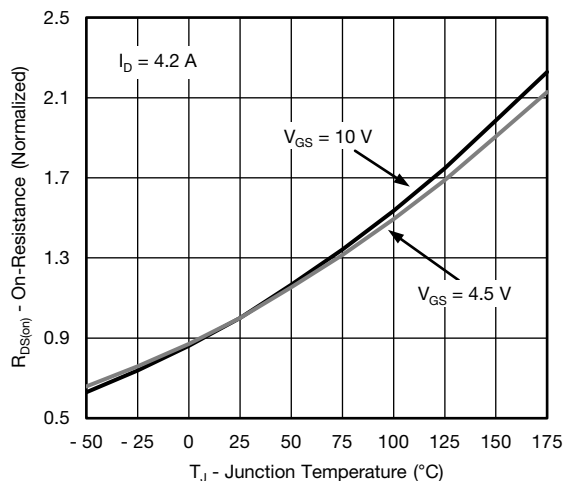
Threshold Voltage



Source Drain Diode Forward Voltage



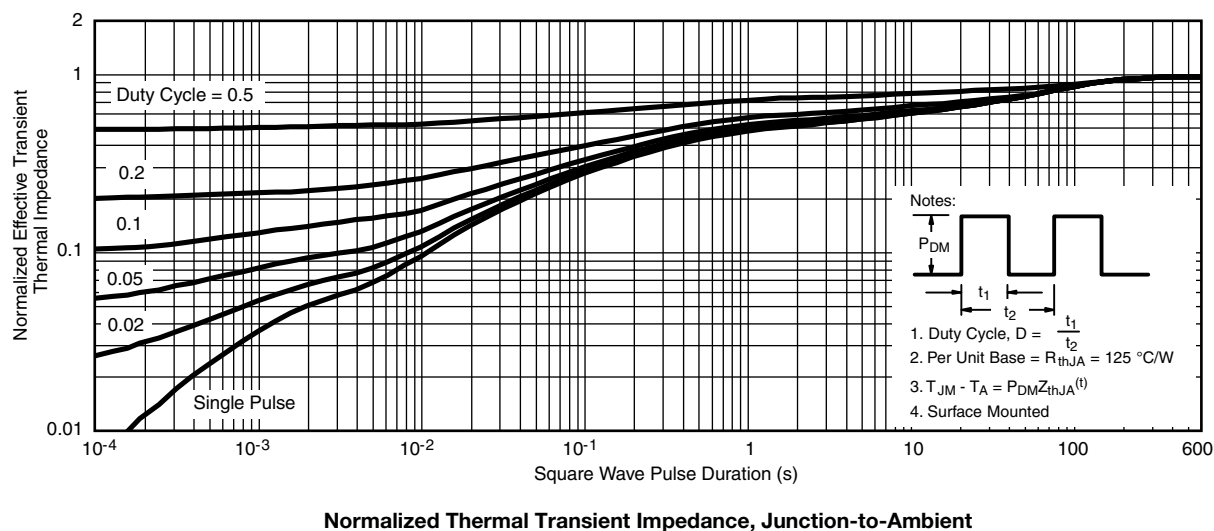
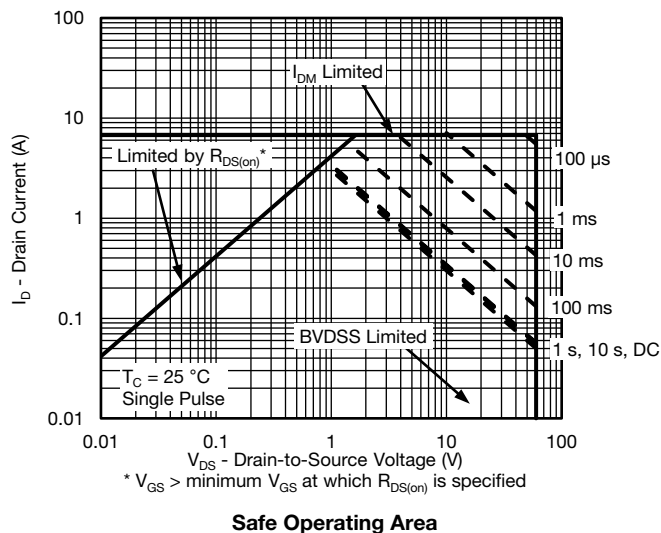
On-Resistance vs. Junction Temperature



On-Resistance vs. Junction Temperature

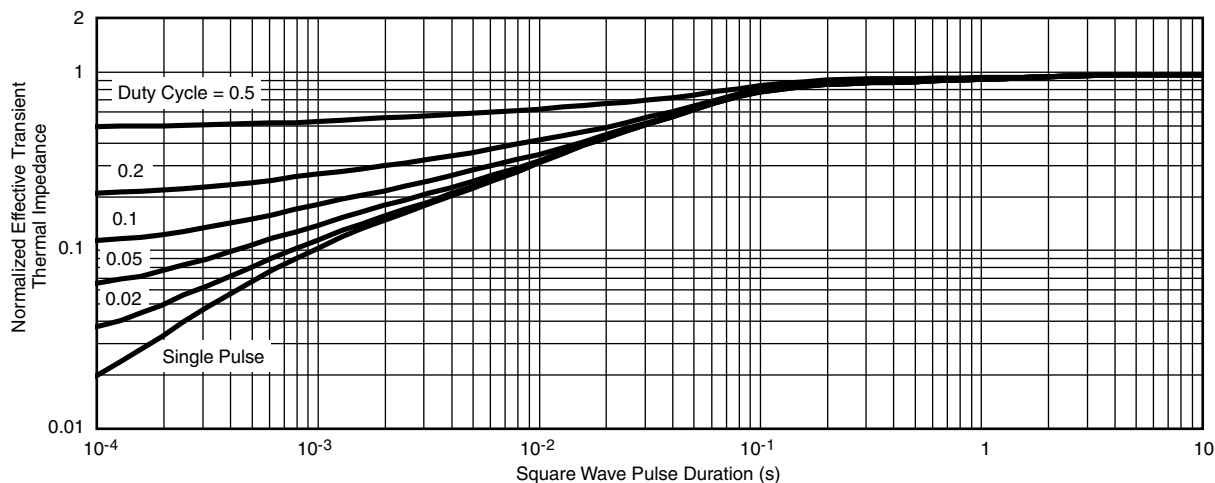


THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)





THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^{\circ}\text{C}$)are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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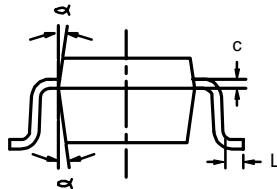
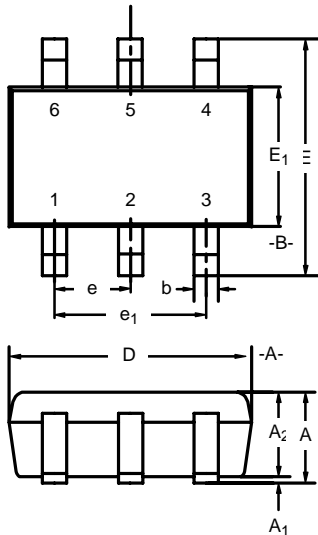
REVISION HISTORY ^a		
REVISION	DATE	DESCRIPTION OF CHANGE
B	05-Nov-15	• Corrected marking code

Note

a. As of April 2014



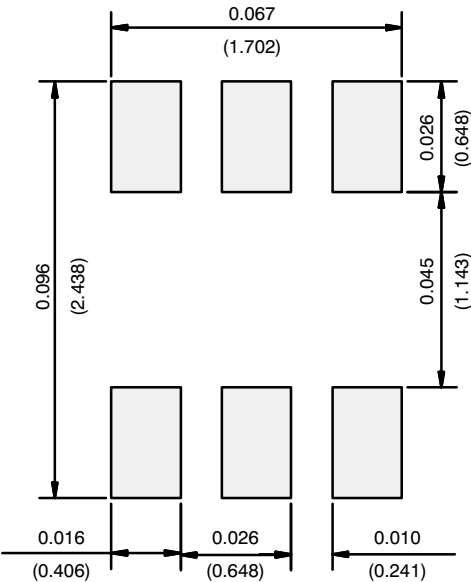
SC-70: 6-LEADS



	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
A	0.90	—	1.10	0.035	—	0.043
A ₁	—	—	0.10	—	—	0.004
A ₂	0.80	—	1.00	0.031	—	0.039
b	0.15	—	0.30	0.006	—	0.012
c	0.10	—	0.25	0.004	—	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.80	2.10	2.40	0.071	0.083	0.094
E ₁	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65BSC			0.026BSC		
e ₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
α	7°Nom			7°Nom		
ECN: S-03946—Rev. B, 09-Jul-01 DWG: 5550						



RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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